

## **Semiconductor Thin Film: Al<sub>x</sub>Ga<sub>1-x</sub>As Epitaxial Layers (Al mole fraction x near 0.30)**

|                 |                                   |
|-----------------|-----------------------------------|
| Art. ID         | NIST-2842                         |
| Unit            | disc                              |
| Deliverydetails | No Dangerous Good /not restricted |

### Description

This Standard Reference Material (SRM®) is intended for use as a reference standard for analytical methods that measure the composition of thin films, such as electron microprobe analysis (EMPA), photoluminescence (PL), auger electron spectroscopy (AES) and X-ray photoelectron spectroscopy (XPS). A unit of NIST-2842 consists of an epitaxial layer of Al<sub>x</sub>Ga<sub>1-x</sub>As with certified Al mole fraction x grown on a gallium arsenide (GaAs) substrate mounted to a stainless steel disk by the use of adhesive tape. Each unit is sealed in a Mylar envelope containing a nitrogen atmosphere. /// Sample value(s) - please ask for current certificate.

| Text/Information      | Analyte/Parameter                            | CAS number | Concentration/Value | Unit | Method | Source |
|-----------------------|--|------------|---------------------|------|--------|--------|
| Individually measured | Certified Value (mole fraction) for Aluminum |            |                     |      |        |        |